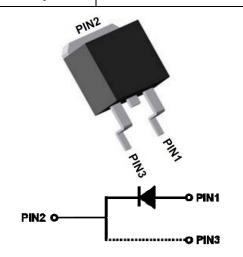






Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F(135°C)}	15A
Q _C	56nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-263

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112010BXYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C			32
Continuous forward current @ T _c =135°C	I _F	А	15
Continuous forward current @ T _C =154°C			10
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	85
Power Dissipation@ T _c =25°C	1	W	136
Power Dissipation@ T _C =110°C	- P _{TOT}		59
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	36
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

YJD112010BXYG4

■Electrical Characteristics (T_a=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =10A, T _j =25°C	1.38	1.60
			I _F =10A, T _j =175°C	1.90	-
Reverse current	I _R	μA	V _R =1200V, T _j =25°C	0.5	25
			V _R =1200V, T _j =175°C	5	-
Total capacitive charge	Q _C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	56	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	774	-
			V _R =400V, f=1MHZ	53	•
			V _R =800V, f=1MHZ	40	-
Capacitance stored energy	Ec	μJ	V _R =800V	16	-

■Thermal Characteristics (Ta=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	1.10

■Typical Characteristics (Typical)

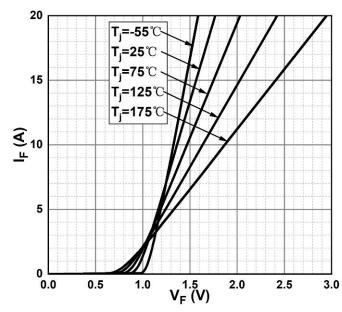


Figure 1. Forward Characteristics

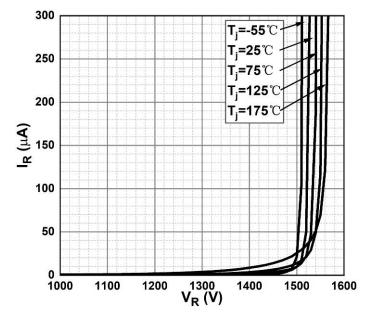
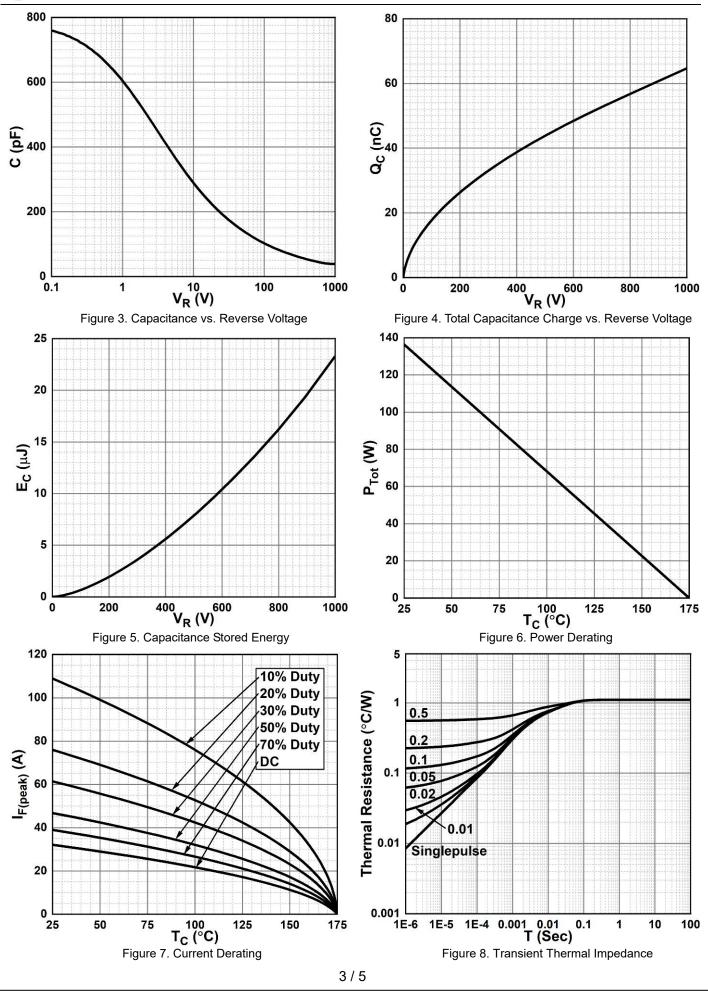


Figure 2. Reverse Characteristics

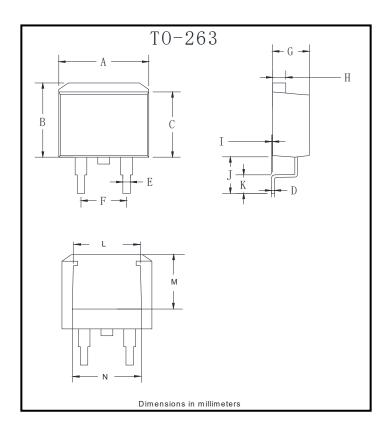
YJD112010BXYG4







■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		



YJD112010BXYG4

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http://www.21yangjie.com, or consult your nearest Yangjie's sales office for further assistance.